

AMENDMENTS TO THE CLAIMS:

1. (Currently amended) A method of polishing and then cleaning ~~a substrate~~ substrates, comprising:

polishing a first substrate by pressing said first substrate against a first polishing surface; then primarily cleaning said first substrate in ~~at least one~~ a first of two first cleaning units; ~~and then~~ secondarily cleaning said first substrate in a common second cleaning unit; ~~wherein said common second cleaning unit is constructed and arranged to receive a substrate from each of said two first cleaning units~~

polishing a second substrate by pressing said second substrate against a second polishing surface; then

primarily cleaning said second substrate in a second of said two first cleaning units; and then secondarily cleaning said second substrate in said common second cleaning unit.

Claims 2-9 (Cancelled)

10. (Currently amended) The method according to claim 9 1, wherein primarily cleaning said first substrate in said ~~second~~ first of said two first cleaning units comprises cleaning said first substrate in said ~~second~~ first of said two first cleaning units by subjecting said first substrate to a first cleaning function, and

primarily cleaning said ~~another~~ second substrate in said ~~first~~ second of said two first cleaning units comprises cleaning said ~~another~~ second substrate in said ~~first~~ second of said two first cleaning units by subjecting said ~~another~~ second substrate to a second cleaning function that is the same as said first cleaning function.

11. (Currently amended) The method according to claim 9 1, further comprising: drying said first substrate and said ~~another~~ second substrate after secondarily cleaning said first substrate and said ~~another~~ second substrate.

12. (Currently amended) The method according to claim 9 1, wherein
primarily cleaning said first substrate and said ~~another~~ second substrate comprises supplying
an etching liquid to said first substrate and said ~~another~~ second substrate, or
secondarily cleaning said first substrate and said ~~another~~ second substrate comprises supplying
an etching liquid to said first substrate and said ~~another~~ second substrate.

13. (Currently amended) The method according to claim 9 1, wherein
primarily cleaning said first substrate in said ~~second~~ first of said two first cleaning units
comprises primarily cleaning said first substrate in said ~~second~~ first of said two first cleaning units for
a time period that is greater than a time period for which said first substrate is secondarily cleaned in
said common second cleaning unit, and
primarily cleaning said ~~another~~ second substrate in said ~~first~~ second of said two first cleaning
units comprises primarily cleaning said ~~another~~ second substrate in said ~~first~~ second of said two first
cleaning units for a time period that is greater than a time period for which said ~~another~~ second
substrate is secondarily cleaned in said common second cleaning unit.

14. (Currently amended) The method according to claim 9 1, wherein
primarily cleaning said first substrate and said ~~another~~ second substrate comprises using ionic
water, ozone water, or hydrogenated water as a cleaning liquid, or
secondarily cleaning said first substrate and said ~~another~~ second substrate comprises using
ionic water, ozone water, or hydrogenated water as a cleaning liquid.

15. (Currently amended) The method according to claim 9 1, wherein
primarily cleaning said first substrate and primarily cleaning said ~~another~~ second substrate
comprises primarily cleaning said first substrate in parallel with primarily cleaning said ~~another~~
second substrate.

Claims 16-21 (Cancelled)

22. (New) The method according to claim 1, wherein polishing said first substrate and polishing said second substrate comprises polishing said first substrate in parallel with polishing said second substrate.

23. (New) The method according to claim 1, further comprising:
not pressing said first substrate against said second polishing surface.

24. (New) The method according to claim 23, further comprising:
not cleaning said first substrate in said second of said two first cleaning units.

25. (New) The method according to claim 24, further comprising:
not pressing said second substrate against said first polishing surface.

26. (New) The method according to claim 25, further comprising:
not cleaning said second substrate in said first of said two first cleaning units.

27. (New) The method according to claim 23, wherein primarily cleaning said first substrate in said first of said two first cleaning units comprises cleaning said first substrate in said first of said two first cleaning units by subjecting said first substrate to a first cleaning function, and

primarily cleaning said second substrate in said second of said two first cleaning units comprises cleaning said second substrate in said second of said two first cleaning units by subjecting said second substrate to a second cleaning function that is the same as said first cleaning function.

28. (New) The method according to claim 23, further comprising:
drying said first substrate and said second substrate after secondarily cleaning said first substrate and said second substrate.

29. (New) The method according to claim 23, wherein
primarily cleaning said first substrate and said second substrate comprises supplying an etching liquid to said first substrate and said second substrate, or
secondarily cleaning said first substrate and said second substrate comprises supplying an etching liquid to said first substrate and said second substrate.

30. (New) The method according to claim 23, wherein
primarily cleaning said first substrate in said first of said two first cleaning units comprises primarily cleaning said first substrate in said first of said two first cleaning units for a time period that is greater than a time period for which said first substrate is secondarily cleaned in said common second cleaning unit, and
primarily cleaning said second substrate in said second of said two first cleaning units comprises primarily cleaning said second substrate in said second of said two first cleaning units for a time period that is greater than a time period for which said second substrate is secondarily cleaned in said common second cleaning unit.

31. (New) The method according to claim 23, wherein
primarily cleaning said first substrate and said second substrate comprises using ionic water, ozone water, or hydrogenated water as a cleaning liquid, or
secondarily cleaning said first substrate and said second substrate comprises using ionic water, ozone water, or hydrogenated water as a cleaning liquid.

32. (New) The method according to claim 23, wherein
primarily cleaning said first substrate and primarily cleaning said second substrate comprises primarily cleaning said first substrate in parallel with primarily cleaning said second substrate.

33. (New) The method according to claim 1, further comprising:
not cleaning said first substrate in said second of said two first cleaning units.